NSN 5962-01-374-6560

Memory Microcircuit - Page 1 of 2



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Between 1.260 inches and 1.280 inches

Body Width:

Between 0.290 inches and 0.310 inches

Body Height:

Between 0.180 inches and 0.200 inches

Maximum Power Dissipation Rating:

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Eo lorops

Features Provided:

Electrostatic sensitive and monolithic and programmed and ultraviolet erasable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Criticality Code Justification:

Feat

Case Outline Source And Designator:

D-9 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed

Voltage Rating And Type Per Characteristic:

7.0 volts power source

Time Rating Per Chacteristic:

30.00 nanoseconds propagation delay time, high to low level output and 30.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Pal

Special Features:

Electrostatic discharge sensitive; altered item, made from p/n 5962-8753901lx, file-name 1061-u58.Jed, checksum a47d; nha p/n 1372ae1061

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type A	and Quantity	/:
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24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0